

1. (Currently Amended) A liquid crystal display (LCD), comprising:
 - a gate line formed on a transparent substrate;
 - a data line crossing said gate line and formed on said transparent substrate;
 - an insulating layer electrically insulating said data line from said gate line;
 - a thin film transistor formed at an intersection of said gate line and said data line, and connected to said gate line and said data line, the thin film transistor being disposed in an area having a channel area, a source area and a drain area;
 - a passivation layer formed over the thin film transistor;
 - a pixel electrode having portions thereof formed on the surface of the passivation layer, but not over the thin film transistor;
 - a low reflective layer formed ~~on for covering~~ at least a portion of at least one of said gate line and said data line ~~and on the area to shield the light passing the gate line, the data line and the area~~; and
 - an upper substrate located above the pixel electrode, wherein an area between said pixel electrode and said upper substrate, and above said low reflective layer, is free of any black matrix or light shielding layer.

2. (Canceled)
3. (Currently Amended) The LCD of claim 26, wherein said low reflective layer is formed on said gate electrode.
4. (Currently Amended) The LCD of claim 3 26, wherein said thin film transistor includes a source electrode and a drain electrode; and said low reflective layer is formed on said source and drain electrodes.
5. (Currently Amended) The LCD of claim [4] 1, wherein said low reflective layer has a light reflectivity of 3% or less.
6. (Currently Amended) The LCD of claim [4] 1, wherein said low reflective layer is formed of CrOx.
7. (Canceled)
8. (Canceled)
9. (Original) The LCD of claim 1, wherein said low reflective layer has a light reflectivity of 3% or less.

10. (Original) The LCD of claim 1, wherein said low reflective layer is formed of CrOx.

11. (Previously Presented) The LCD of claim 1, wherein said passivation layer formed over said gate line, said data line, said low reflective layer and said pixel electrode formed on said passivation layer is connected via a contact hole in said passivation layer to said thin film transistor.

12. (Original) The LCD of claim 11, wherein said pixel electrode is formed over a portion of said data line.

13. (Original) The LCD of claim 11, wherein said pixel electrode is formed over a portion of said gate line.

14. (Original) The LCD of claim 11, further comprising:
a color filter substrate with color filters formed thereon; and
liquid crystal sealed between said color filter substrate and said transparent substrate.

15. (Currently Amended) A method of manufacturing a liquid crystal display, comprising:

forming a gate line and ~~a portion protruding from said gate line to serve as~~ a gate electrode of a thin film transistor ~~to be connected with the gate line~~ on a transparent substrate;

forming an insulating layer electrically insulating said gate line ~~and the gate electrode~~;

forming a data line ~~and source electrode and drain electrode~~ over said transparent substrate ~~and crossing said gate line the source electrode and the drain electrode being respectively disposed in a source area and a drain area, at least one electrode of the source electrode and the drain electrode being connected with the data line~~;

forming a passivation layer over the thin film transistor;

forming a pixel electrode with portions thereof on the surface of the passivation layer, but not over the thin film transistor;

first forming a low reflective layer over at least a portion of at least one of said gate line and said data line ~~and on the channel region, the source area and the drain area~~;

forming an upper substrate above the pixel electrode, wherein an area between said pixel electrode and said upper substrate, and above said low reflective layer, is free of any black matrix or light shielding layer.

16. (Canceled)

17. (Currently Amended) The method of claim 16 15, wherein ~~said second~~
~~the low reflective layer forming~~ step forms ~~said~~ ~~includes the step of forming~~ a low
reflective layer ~~over covering~~ said gate electrode.

18. (Canceled)

19. (Currently Amended) The method of claim 15, wherein ~~said forming a~~
~~data line~~ ~~step forms a portion protruding from~~ ~~said data line~~ to serve as a source
electrode of a thin film transistor, and

~~said first forming step forms~~ ~~said low reflective layer~~ ~~over is formed covering~~
said source electrode.

20. (Original) The method of claim 15, wherein ~~said low reflective layer~~ has
a light reflectivity of 3% or less.

21. (Original) The method of claim 15, wherein ~~said low reflective layer~~ is
formed of CrOx.

22. (Currently Amended) A method of manufacturing a liquid crystal display, comprising:

forming a gate line and gate electrode connected thereto on a transparent substrate;

forming an insulating layer over said gate line and gate electrode;

forming a semiconductor layer over said gate electrode;

forming a data line crossing said gate line, a source electrode connected to said data line and on a first portion of said semiconductor layer, and a drain electrode on a second portion of said semiconductor layer;

forming a low reflective layer over at least a portion of at least one of said gate line and said data line and on the first and second regions;

forming a passivation layer having a contact hole exposing said drain electrode over said transparent substrate;

forming a pixel electrode with portions thereof disposed on said passivation layer but not over the thin film transistor, and connected to said drain electrode via said contact hole; and

forming an upper substrate above the pixel electrode, wherein an area between said pixel electrode and said upper substrate, and above said low reflective layer, is free of any black matrix or light shielding.

23. (Original) The method of claim 22, wherein said forming a pixel electrode step forms said pixel electrode to overlap a portion of said data line.

24. (Original) The method of claim 22, wherein said forming a pixel electrode step forms said pixel electrode to overlap a portion of said gate line.

25. (Previously Presented) The method of claim 22, further comprising:
forming a color filter on a color filter substrate; and
sealing the liquid crystal between said color filter substrate and said transparent substrate.

26. (New) The LCD of claim 1, wherein the thin film transistor further includes:

a gate electrode connected to said gate line, said gate electrode being covered with the channel region; and

a source electrode and a drain electrode connected to the drain line, the source electrode and the drain electrode being respectively covered with the source region and the drain region.